









CD74HCT86, CD54HCT86

JAJSMC3A - JUNE 2020 - REVISED AUGUST 2024

CDx4HCT86 クワッド 2 入力 XOR ゲート

1 特長

- LSTTL 入力ロジック互換
 - $V_{IL(max)} = 0.8V$, $V_{IH(min)} = 2V$
- CMOS 入力ロジック互換
 - I_I ≤ 1 μ A (V_{OL} , V_{OH})
- バッファ付き入力
- 4.5V~5.5Vで動作
- 広い動作温度範囲:-55°C~+125℃
- 最大 10 個の LSTTL 負荷ファンアウトに対応
- LSTTL ロジック IC に比べて消費電力を大幅削減

2 アプリケーション

- 複数の入力信号の位相差を検出
- 選択可能なインバータ/バッファの作成

3 概要

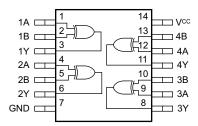
このデバイスには、4 つの独立した 2 入力 XOR ゲートが 内蔵されています。各ゲートはブール関数 Y = A

B を 正論理で実行します。

製品情報

部品番号	パッケージ ⁽¹⁾	パッケージ サイズ ⁽²⁾	本体サイズ ⁽³⁾		
	D (SOIC, 14)	8.65mm × 6mm	8.65mm × 3.9mm		
CDx4HCT86	N (PDIP, 14)	19.30mm × 9.4mm	19.30mm × 6.35mm		
	J (CDIP, 14)	19.56mm × 6.7mm	19.56mm × 4.57mm		

- 詳細については、「メカニカル、パッケージ、および注文情報」を参 照してください。
- パッケージ サイズ (長さ×幅) は公称値であり、該当する場合はピ (2) ンも含まれます。
- 本体サイズ (長さ×幅) は公称値であり、ピンは含まれません。 (3)



機能的なピン配置



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4 Pin Configuration and Functions

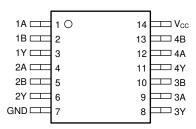


図 4-1. D, N, or J Package 14-Pin SOIC, PDIP, or CDIP Top View

	PIN	TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.	- ITPE\'7	DESCRIPTION
1A	1	Input	Channel 1, Input A
1B	2	Input	Channel 1, Input B
1Y	3	Output	Channel 1, Output Y
2A	4	Input	Channel 2, Input A
2B	5	Input	Channel 2, Input B
2Y	6	Output	Channel 2, Output Y
GND	7	_	Ground
3Y	8	Output	Channel 3, Output Y
3A	9	Input	Channel 3, Input A
3B	10	Input	Channel 3, Input B
4Y	11	Output	Channel 4, Output Y
4A	12	Input	Channel 4, Input A
4B	13	Input	Channel 4, Input B
V _{CC}	14	_	Positive Supply

⁽¹⁾ Signal Types: I = Input, O = Output, I/O = Input or Output



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$		±20	mA
lok	Output clamp current ⁽²⁾		±20	mA	
Io	Continuous output current	$V_{O} > -0.5 \text{ V or } V_{O} < V_{CC} + 0.5 \text{ V}$		±25	mA
	Continuous current through V _{CC} or GND			±50	mA
TJ	Junction temperature ⁽³⁾			150	°C
	Lead temperature (soldering 10s)	SOIC - lead tips only		300	°C
T _{stg}	Storage temperature	-65	150	°C	

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Rating may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Condition. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/ JEDEC JS-001 ⁽¹⁾	±2000	\/
V _(ESD)	Electrostatic discriarge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V

JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT	
V _{CC}	Supply voltage		4.5		5.5	V	
V _{IH}	High-level input voltage	V _{CC} = 4.5 V to 5.5 V	2			V	
V _{IL}	Low-level input voltage	V _{CC} = 4.5 V to 5.5 V			0.8	V	
VI	Input voltage		0		V_{CC}	V	
Vo	Output voltage		0		V _{CC}	V	
	Input transition time	V _{CC} = 4.5 V			500		
l _t	Input transition time	V _{CC} = 5.5 V			400	ns	
T _A	Operating free-air temperature		– 55		125	°C	

5.4 Thermal Information

		CD74I		
THERMAL METRIC ⁽¹⁾		N (PDIP)	D (SOIC)	UNIT
		14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	103.8	138.7	°C/W
R _{θJC(top)} Junction-to-case (top) thermal resistance		91.6	93.8	°C/W

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English Data Sheet: SCHS410

The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

Guaranteed by design.

JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



		CD74	CD74HCT86				
	THERMAL METRIC(1)	N (PDIP)	D (SOIC)	UNIT			
		14 PINS	14 PINS				
R _{θJB}	Junction-to-board thermal resistance	83.5	94.7	°C/W			
Ψ_{JT}	Junction-to-top characterization parameter	71.1	49.1	°C/W			
Ψ_{JB}	Junction-to-board characterization parameter	83.4	94.3	°C/W			
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W			

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

5.5 Electrical Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

					Operating free-air temperature (T _A)									
	PARAMETER	TEST CONDITIONS		V _{cc}		25°C		-40°	C to 85	s°C	-55°C	C to 125	5°C	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
V _{OH}	High-level output	V _I = V _{IH} or V _{IL}	I _{OH} = -20 μΑ	4.5 V	4.4			4.4			4.4			V
	voitage	VIL.	I _{OH} = -4 mA	4.5 V	3.98			3.84			3.7			
V _{OL}	Low-level output	V _I = V _{IH} or	I _{OL} = 20 μA	4.5 V			0.1			0.1			0.1	V
VOL	voltage	V _{IL}	I _{OL} = 4 mA	4.5 V			0.26			0.33			0.4	v
I	Input leakage current	V _I = V _{CC} and GND	I _O = 0	5.5 V			±0.1			±1			±1	μA
I _{CC}	Supply current	V _I = V _{CC} or GND	I _O = 0	5.5 V			2			20			40	μA
ΔI _{CC}	Additional Quiescent Device Current Per Input Pin.	V _I = V _{CC} - 2.1		4.5 V to 5.5 V		100	360			450			490	μА
Ci	Input capacitance		•	5 V			10			10			10	pF

⁽¹⁾ For dual-supply systems theoretical worst case ($V_I = 2.4 \text{ V}$, $V_{CC} = 5.5 \text{ V}$) specification is 1.8 mA.

5.6 Switching Characteristics

over operating free-air temperature range; typical values measured at TA = 25°C (unless otherwise noted).

	1 3 1		3 / /1	TEST		Operating free-air temperature (T _A)									
	PARAMETER	FROM	то	CONDITIO			25°C		-40°	C to 8	5°C	-55°C	C to 12	25°C	UNIT
				NS		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
+ .	Propagation delay	A or B	Υ	C _L = 50 pF	4.5 V			32			40			48	ns
t _{pd}	Propagation delay	A or B	Υ	C _L = 15 pF	5 V		13								115
t _t	Transition-time		Υ	C _L = 50 pF	4.5 V			15			19			22	ns

5.7 Operating Characteristics

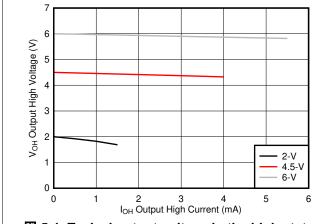
over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

	0 / 31				
PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP MAX	UNIT
C _{pd} Power dissipation capacitance per gate	No load	5 V		27	pF

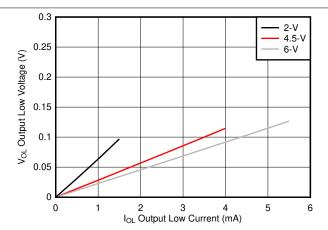


5.8 Typical Characteristics

 $T_A = 25^{\circ}C$



 ${f Z}$ 5-1. Typical output voltage in the high state (${f V}_{OH}$)

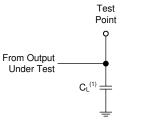


 ${\color{red} {\Bbb Z}}$ 5-2. Typical output voltage in the low state (${\color{red} {V}_{OL}}$)



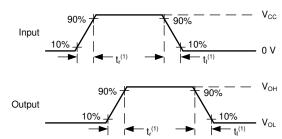
6 Parameter Measurement Information

- Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_t < 6 ns.
- · The outputs are measured one at a time, with one input transition per measurement.



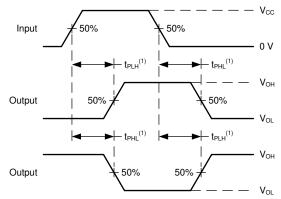
A. C_L = 50 pF and includes probe and jig capacitance.

図 6-1. Load Circuit



A. t_t is the greater of t_r and t_f.

図 6-2. Voltage Waveforms Transition Times



A. The maximum between t_{PLH} and t_{PHL} is used for t_{pd}.

図 6-3. Voltage Waveforms Propagation Delays

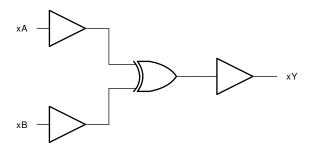


7 Detailed Description

7.1 Overview

This device contains four independent 2-input XOR gates. Each gate performs the Boolean function $Y = A \oplus B$ in positive logic.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Balanced CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the ### 5.1 must be followed at all times.

The CD74HCT86 can drive a load with a total capacitance less than or equal to the maximum load listed in the $\frac{1}{2}\frac{1}{2}\frac{1}{2}\frac{1}{2}$ 5.6 connected to a high-impedance CMOS input while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed the provided load value. If larger capacitive loads are required, it is recommended to add a series resistor between the output and the capacitor to limit output current to the values given in the $\frac{1}{2}\frac{1}{2}\frac{1}{2}\frac{1}{2}$.

7.3.2 TTL-Compatible CMOS Inputs

TTL-Compatible CMOS inputs are high impedance and are typically modeled as a resistor from the input to ground in parallel with the input capacitance given in the $2/2 \times 5.5$. The worst case resistance is calculated with the maximum input voltage, given in the $2/2 \times 5.5$, and the maximum input leakage current, given in the $2/2 \times 5.5$, using ohm's law (R = V ÷ I).

Signals applied to the inputs need to have fast edge rates, as defined by $\Delta t/\Delta v$ in the $2/2 \pm 2/5.3$ to avoid excessive current consumption and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be used to condition the input signal prior to the TTL-compatible CMOS input.



7.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in 🗵 7-1.

注意

Voltages beyond the values specified in the $2/2 \le 5.1$ table can cause damage to the device. The recommended input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

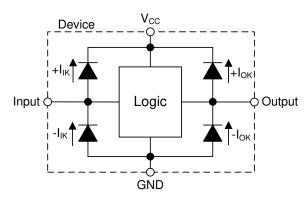


図 7-1. Electrical Placement of Clamping Diodes for Each Input and Output

7.4 Device Functional Modes

表 7-1. Function Table

INPU	ITS ⁽¹⁾	OUTPUT ⁽²⁾
Α	В	Y
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

- (1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care
- (2) H = Driving High, L = Driving Low, Z = High Impedance State

8 Application and Implementation

注

以下のアプリケーション情報は、TIの製品仕様に含まれるものではなく、TIではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

8.1 Application Information

In this application, a 2-input XOR gate is used as a phase difference detector as shown in \mathbb{Z} 8-1. The remaining three gates can be used for other applications in the system, or the inputs can be grounded and the channels left unused.

The device is used to identify phase difference between a reference clock and another input clock. Whenever the clock states are different, the XOR output will pulse HIGH until the clocks return to the same state. The output is fed into a low-pass filter to obtain a DC representation of the phase difference.

8.2 Typical Application

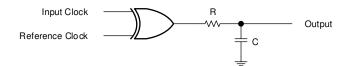


図 8-1. Typical application schematic

8.2.1 Design Requirements

8.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the $\frac{1}{2}\frac{1}{2}\frac{1}{2}$ 5.3. The supply voltage sets the device's electrical characteristics as described in the $\frac{1}{2}\frac{1}{2}\frac{1}{2}$ 5.5.

The supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the CD74HCT86 plus the maximum supply current, I_{CC} , listed in the $\forall 2/2 \geq 5.5$. The logic device can only source or sink as much current as it is provided at the supply and ground pins, respectively. Be sure not to exceed the maximum total current through GND or V_{CC} listed in the $\forall 2/2 \geq 5.1$.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and C_{pd} Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.

注意

The maximum junction temperature, $T_J(max)$ listed in the $2/2 \le 5.1$, is an additional limitation to prevent damage to the device. Do not violate any values listed in the $2/2 \le 5.1$. These limits are provided to prevent damage to the device.

8.2.1.2 Input Considerations



Refer to the セクション 7.3 for additional information regarding the inputs for this device.

8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the $\frac{1}{2}\frac{1}{2}\frac{1}{2}\frac{1}{2}\frac{1}{2}$. Similarly, the ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the $\frac{1}{2}\frac{1}{2}\frac{1}{2}\frac{1}{2}\frac{1}{2}\frac{1}{2}\frac{1}{2}$.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to セクション 7.3 for additional information regarding the outputs for this device.

8.2.2 Detailed Design Procedure

- 1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the セクション 8.4.
- Ensure the capacitive load at the output is ≤ 70 pF. This is not a hard limit, however it will ensure optimal
 performance. This can be accomplished by providing short, appropriately sized traces from the CD74HCT86
 to the receiving device.
- 3. Ensure the resistive load at the output is larger than (V_{CC} / I_O(max)) Ω. This will ensure that the maximum output current from the セクション 5.1 is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
- Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase
 can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd
 Calculation

8.2.3 Application Curves

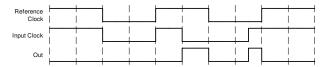


図 8-2. Typical application timing diagram

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the $\forall \not \sim 5.3$. Each V_{CC} terminal should have a bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in $\boxtimes 8-3$.

8.4 Layout

8.4.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

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8.4.2 Layout Example

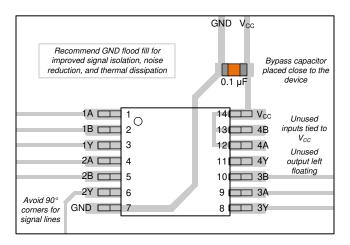


図 8-3. Example layout for the CD74HCT86



9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation see the following:

- HCMOS Design Considerations
- CMOS Power Consumption and CPD Calculation
- · Designing with Logic

9.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。 変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

9.3 サポート・リソース

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9.6 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
5962-8984401CA	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8984401CA CD54HCT86F3A
CD54HCT86F	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	CD54HCT86F
CD54HCT86F.A	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	CD54HCT86F
CD54HCT86F3A	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8984401CA CD54HCT86F3A
CD54HCT86F3A.A	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8984401CA CD54HCT86F3A
CD74HCT86E	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-55 to 125	CD74HCT86E
CD74HCT86E.A	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-55 to 125	CD74HCT86E
CD74HCT86EE4	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-55 to 125	CD74HCT86E
CD74HCT86M	Obsolete	Production	SOIC (D) 14	-	-	Call TI	Call TI	-55 to 125	HCT86M
CD74HCT86M96	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU SN NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT86M
CD74HCT86M96.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT86M
CD74HCT86MT	Obsolete	Production	SOIC (D) 14	-	-	Call TI	Call TI	-55 to 125	HCT86M

⁽¹⁾ Status: For more details on status, see our product life cycle.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE OPTION ADDENDUM

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Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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OTHER QUALIFIED VERSIONS OF CD54HCT86, CD74HCT86:

Catalog : CD74HCT86

Military: CD54HCT86

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO PI BO BO Cavity AO

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

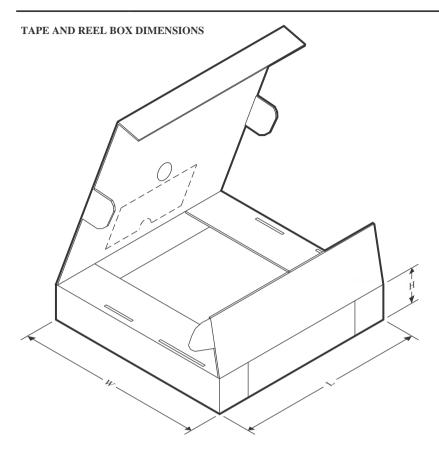


*All dimensions are nominal

Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HCT86M96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
ı	CD74HCT86M96	SOIC	D	14	2500	353.0	353.0	32.0	

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CD74HCT86E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HCT86E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HCT86E.A	N	PDIP	14	25	506	13.97	11230	4.32
CD74HCT86E.A	N	PDIP	14	25	506	13.97	11230	4.32
CD74HCT86EE4	N	PDIP	14	25	506	13.97	11230	4.32
CD74HCT86EE4	N	PDIP	14	25	506	13.97	11230	4.32



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



CERAMIC DUAL IN LINE PACKAGE



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4040083-5/G





CERAMIC DUAL IN LINE PACKAGE



NOTES:

- 1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This package is hermitically sealed with a ceramic lid using glass frit.
- His package is remitted by sealed with a ceramic its using glass mit.
 Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
 Falls within MIL-STD-1835 and GDIP1-T14.



CERAMIC DUAL IN LINE PACKAGE



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



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